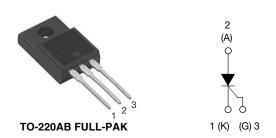


## VS-25TTS..FPPbF Series, VS-25TTS..FP-M3 Series

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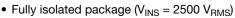
# Thyristor High Voltage, Phase Control SCR, 25 A

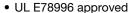


PRODUCT SUMMARY				
Package	TO-220AB FP			
Diode variation	Single SCR			
I <sub>T(AV)</sub>	16 A			
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V			
V <sub>TM</sub>	1.25 V			
I <sub>GT</sub>	45 mA			
$T_J$	-40 °C to 125 °C			

#### **FEATURES**







• 125 °C max. operating junction temperature

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE

#### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

### **DESCRIPTION**

The VS-25TTS...FP... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS					
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	18	22	А		

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I <sub>T(AV)</sub>	Sinusoidal waveform	16	۸		
I <sub>RMS</sub>		25	Α		
V <sub>RRM</sub> /V <sub>DRM</sub>		800/1200	V		
I <sub>TSM</sub>		350	A		
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V		
dV/dt		500	V/µs		
dl/dt		150	A/μs		
T <sub>J</sub>		-40 to 125	°C		

VOLTAGE RATINGS						
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA			
VS-25TTS08FPPbF, VS-25TTS08FP-M3	800	800	10			
VS-25TTS12FPPbF, VS-25TTS12FP-M3	1200	1200	10			

Revision: 13-May-16 1 Document Number: 94384



# VS-25TTS..FPPbF Series, VS-25TTS..FP-M3 Series

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2.2	0			VALUES	
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 51 °C, 180° conduction half sine wave	16	6	
Maximum RMS on-state current	I <sub>RMS</sub>			5	Α
Maximum peak, one-cycle,		10 ms sine pulse, rated V <sub>RRM</sub> applied	300	0	А
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied	350	0	
Maximum I <sup>2</sup> t for fusing	I <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	450	0	A <sup>2</sup> s
Maximum i-t for fusing	1-1	10 ms sine pulse, no voltage reapplied		0	A-S
Maximum I <sup>2</sup> √t for fusing	l²√t	t = 0.1ms to 10 ms, no voltage reapplied		00	A²√s
Maximum on-state voltage drop	$V_{TM}$	16 A, T <sub>J</sub> = 25 °C		5	V
On-state slope resistance	r <sub>t</sub>	—— T <sub>J</sub> = 125 °C		0	mΩ
Threshold voltage	V <sub>T(TO)</sub>			)	V
Maximum rayaraa and direct laakaga aurrant	1 /1	$T_J = 25 ^{\circ}\text{C}$	0.5	5	
Maximum reverse and direct leakage current	$I_{RM}/I_{DM}$	$T_{\rm J} = 125 ^{\circ}{\rm C}$ $V_{\rm R} = {\rm Rated}  {\rm V}_{\rm RRM} / {\rm V}_{\rm DRM}$		)	
Holding current	I <sub>H</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $I_J$ = 25 °C		150	mA
Maximum latching current	Ι <sub>L</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C 200		0	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 \text{ %, } V_{DRM} = R_g - k = Open$ 500		0	V/µs
Maximum rate of rise of turned-on current	dl/dt	150		A/µs	

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	$P_{GM}$		8.0	W	
Maximum average gate power	P <sub>G(AV)</sub>		2.0	] <sup>vv</sup>	
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α	
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V	
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	60	mA	
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	45		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	20		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	2.5		
Maximum required DC gate voltage to trigger	$V_{\mathrm{GT}}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	1 ,,	
voltage to angger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V	
Maximum DC gate voltage not to trigger	$V_{GD}$	T 405 00 V Polesterie	0.25		
Maximum DC gate current not to trigger	I <sub>GD</sub>	I <sub>GD</sub> T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value		mA	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9		
Typical reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C	4	μs	
Typical turn-off time	t <sub>q</sub>	1J = 120 0	110		



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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		$T_J$ , $T_{Stg}$		-40 to 125	°C
Maximum thermal resistance, junction to case		$R_{\text{thJC}}$	DC operation	2.5	
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		62	°C/W
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	OZ.
Mounting torque	minimum			6 (5)	kgf · cm
	maximum			12 (10)	(lbf · in)
Marking device			Occasional TO COO AD FULL DAIX (CAA)(C)	25TTS08	BFP
			Case style TO-220AB FULL-PAK (94/V0)	25TTS12FP	

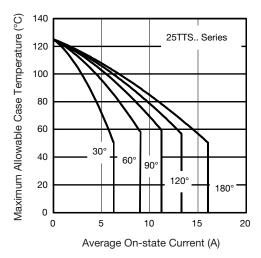


Fig. 1 - Current Rating Characteristics

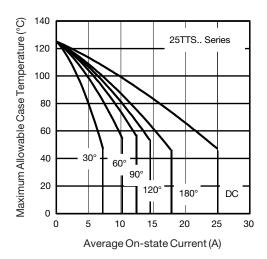


Fig. 2 - Current Rating Characteristics

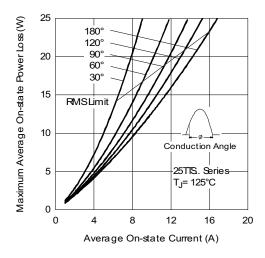


Fig. 3 - On-State Power Loss Characteristics

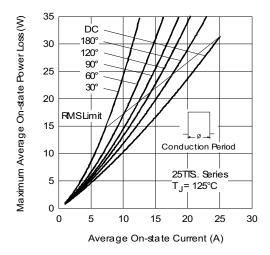


Fig. 4 - On-State Power Loss Characteristics



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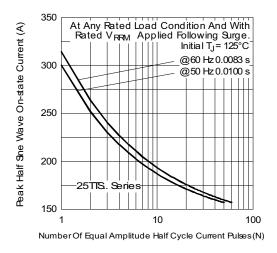


Fig. 5 - Maximum Non-Repetitive Surge Current

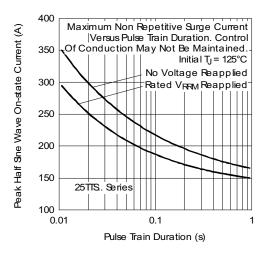


Fig. 6 - Maximum Non-Repetitive Surge Current

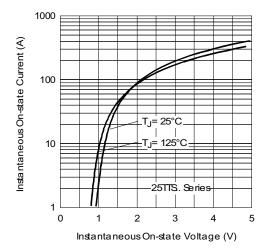


Fig. 7 - On-State Voltage Drop Characteristics

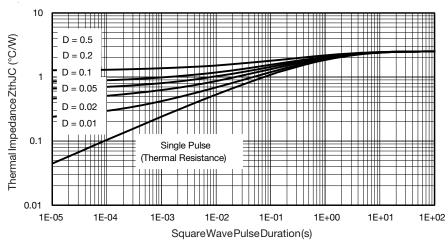
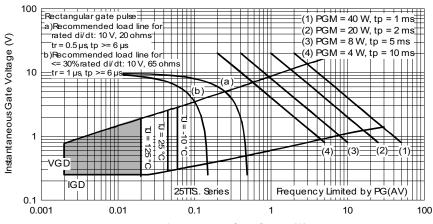


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

# VS-25TTS..FPPbF Series, VS-25TTS..FP-M3 Series

### Vishay Semiconductors

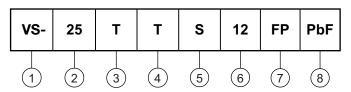


Instantaneous Gate Current (A)
Fig. 9 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

www.vishay.com

### Device code



- 1 Vishay Semiconductors product
- 2 Current rating (25 = 25 A)
- 3 Circuit configuration:

T = Single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

Standard recovery rectifier

7 - FULL-PAK

8 - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

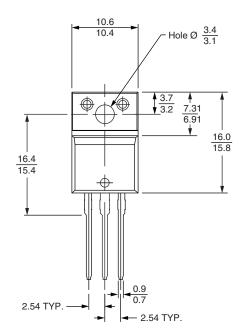
ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-25TTS08FPPbF	50	1000	Antistatic plastic tubes		
VS-25TTS08FP-M3	50	1000	Antistatic plastic tubes		
VS-25TTS12FPPbF	50	1000	Antistatic plastic tubes		
VS-25TTS12FP-M3	50	1000	Antistatic plastic tubes		

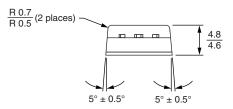
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95072</u>					
Dort marking information	TO-220FP PbF	www.vishay.com/doc?95069			
Part marking information	TO-220FP -M3	www.vishay.com/doc?95456			

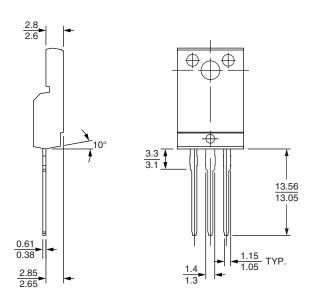


# Vishay Semiconductors

### **DIMENSIONS** in millimeters







### Lead assignments

#### **Diodes**

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220 FULL-PAK

## **Legal Disclaimer Notice**



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